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# P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)(Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)		
- 30	10 at V <sub>GS</sub> = - 10 V	- 50	43 nC		
- 30	14 at V <sub>GS</sub> = - 4.5 V	- 50 43 110	43110		

#### **FEATURES**

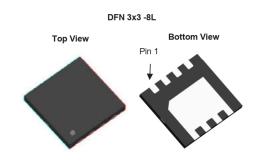
- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested
- Low On-Resistance for Low Voltage Drop

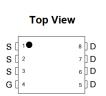
# Pb free

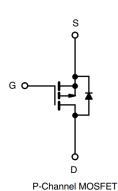
RoHS

#### **APPLICATIONS**

- · Battery, Load and Adaptor Switches
  - Notebook Computers
  - Notebook Battery Packs







ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V <sub>DS</sub>	- 30	V		
Gate-Source Voltage	$V_{GS}$	± 20	V		
Continuous Dusin Comment /T 150 °C\2	T <sub>C</sub> = 25 °C		- 50	A	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>C</sub> = 100 °C	□ I <sub>D</sub>	- 34		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	- 200			
Single Avalanche Energy	E <sub>AS</sub>	38	mJ		
Maximum Power Dissipation <sup>c</sup>	T <sub>C</sub> = 25 °C	D	48	W	
iwaximum Fower Dissipation	T <sub>C</sub> = 100 °C	P <sub>D</sub>	19.2		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) <sup>d</sup>	R <sub>thJA</sub>	25	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	2.6			

#### **Notes**

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>8JA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = -250 \mu A$	- 30			V
Gate-Source Threshold Voltage	V <sub>G</sub> S(th)	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.2		- 2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V			- 1	
Zero Gate Voltage Drain Gurrent		V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 5	μA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 50			Α
Dualis Courses On Otata Basistanas	D	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 15 A		10	12	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 10 A		14	16	mΩ
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 15 A		45		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>			3810		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		446		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	1		345		
Total Gate Charge	Qg			43		
Gate-Source Charge	$Q_{gs}$	$Q_{gs}$ $V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -10 \text{ A}$		13.5		nC
Gate-Drain Charge	$Q_{gd}$			28		1
Gate Resistance	$R_{g}$	f = 1 MHz		3		Ω
Turn-On Delay Time	t <sub>d(on)</sub>			15		
Rise Time	t <sub>r</sub>	$V_{DD} = -15 \text{ V, R}_{L} = 1.5 \Omega$		12		1
Turn-Off DelayTime	t <sub>d(off)</sub>	$I_D \cong -10 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1\Omega$		58		- ns
Fall Time	t <sub>f</sub>			12		1
Drain-Source Body Diode Characterist	ics					
Continous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 50	Α
Pulse Diode Forward Current	I <sub>SM</sub>				- 200	
Body Diode Voltage	$V_{SD}$	I <sub>S</sub> = - 1 A			- 1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -10 A, dI/dt = 100 A/μs, Τ <sub>I</sub> = 25 °C		18		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$	1- 1071, and = 10071 po, 13 = 20 0		25		nC

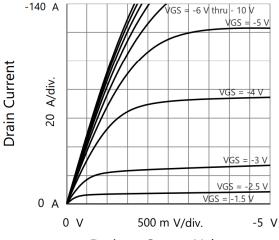
#### Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

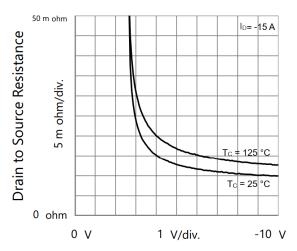
a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing.



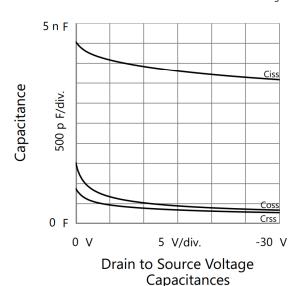
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

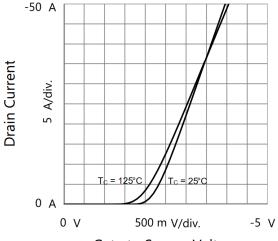


Drain to Source Voltage Output Characteristics

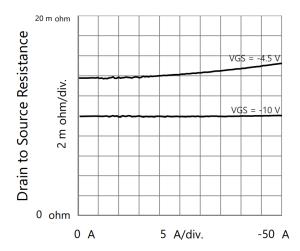


Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage

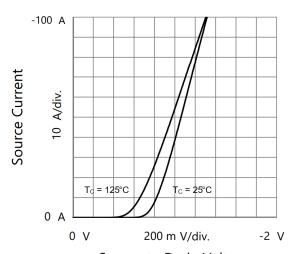




Gate to Source Voltage Transfer Characteristics



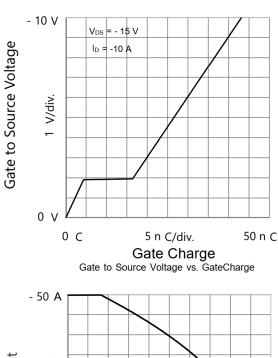
Drain Current
Drain to Source Resistance vs. Drain Current

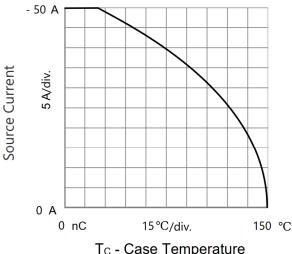


Source to Drain Voltage Body Diode Forward Characteristics

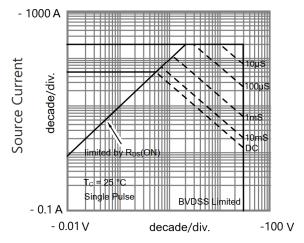


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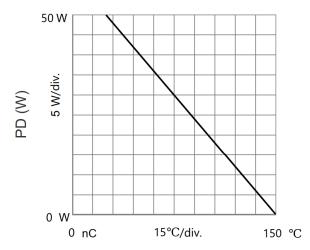




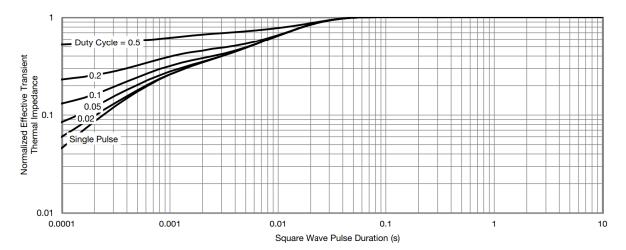




Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



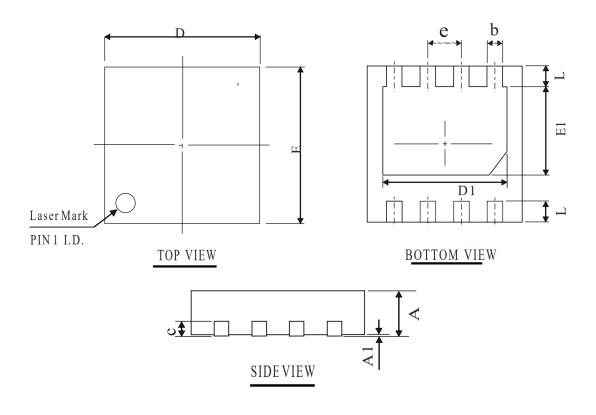
 $T_{C}$  - Case Temperature  $_{\text{Power Derating}}$ 



Normalized Thermal Transient Impedance, Junction-to-Case



# DFN3\*3-8L PACKAGE OUTLINE



## COMMONDIMENSIONS (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0. 60	0.75	0. 90
A1	0. 00	0.02	0. 08
ь	0. 20	0.30	0.45
D	2.85	3.00	3. 15
Е	2. 85	3.00	3. 15
D1	2. 10	2.40	2. 70
E1	1.50	1.70	2.00
L	0. 20	0.40	0.60
С	0. 203 REF		
e	0. 65 BSC		

## OTHER DIMENSIONS

A	0. 50	0.55	0.60
A	0.40	0.45	0. 50

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